1N914B

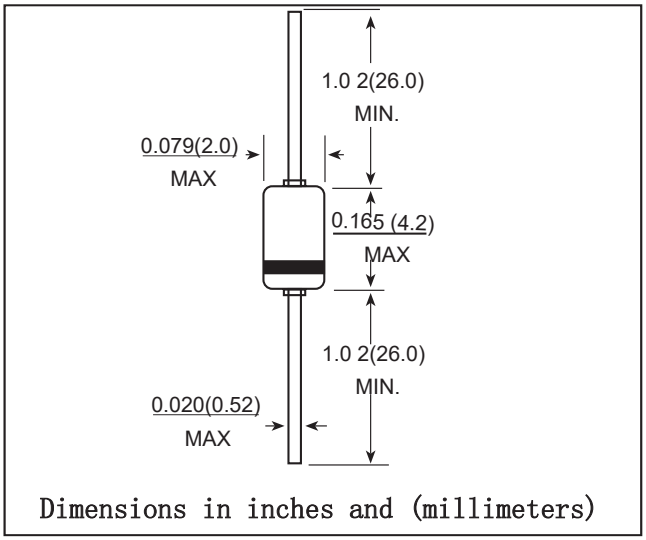
DO-35 Glass Switching Diode

Features

- Fast Switching Device (TRR <4.0 nS)
- Power Dissipation of 500mW
- High Stability and High Reliability
- Low reverse leakage

Mechanical Data

- Case: DO-35 Glass Case
- Polarity: Color band denotes cathode end
- Mounting Position: Any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameters	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Power Dissipation	Pd	500	mW
Operating junction temperature	Tj	175	℃
Storage temperature range	Ts	-65-+200	℃
Working Inverse Voltage	W_{IV}	75	V
Average Rectified Current	I_O	150	mA
Non-repetitive Peak Forward Current @ t<1s and Tj=25℃	I_{FM}	450	mA

Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

Electrical Specification (T_A=25°C unless otherwise specified)

Symbols	Parameter	Test Condition	Limits		Unit
			Min	Max	
B_V	Breakdown Voltage	IR=100uA	100		V
		IR=5uA	75		
I_R	Reverse Leakage Current	VR=20V	---	25	nA
		VR=75	---	5	uA
V_F	Forward Voltage 1N4448/1N914B	IF=5mA	0.62	0.72	V
	Forward Voltage 1N4148	IF=10mA	---	1	
	Forward Voltage 1N4448/1N914B	IF=100mA	---	1	
T_{RR}	Reverse Recovery Time	IF= 10mA, IR=1.0mA RL=100Ω IRR=1mA	---	4	nS
C	Capacitance	VR=0V, f=1MHZ	---	4	pF